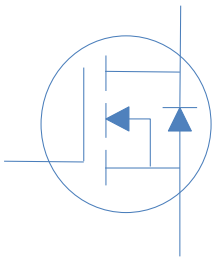
45V N-Ch Power MOSFET

DS(on),typ				Ω
DS(on),typ				Ω
DS(on),typ				Ω
DS(on),typ				Ω



=25 (unless otherwise specified)

		=25		
		=100		
		=25		
Avalanche Energy, Single Pulse		=25		
Power Dissipation		=25		
Operating and Storage Temperature				

Thermal Resistance Junction-Ambient	θ		/W
Thermal Resistance Junction-Case	θ		/W

Fig 1. Typical Output Characteristics

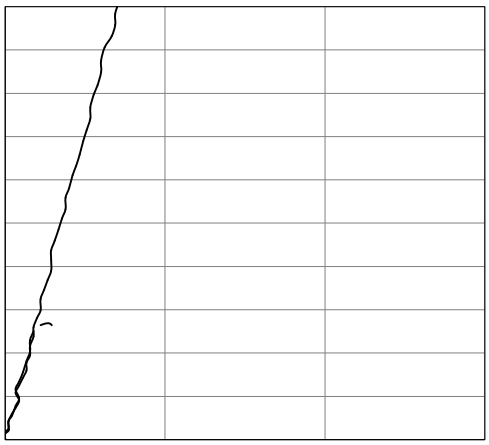


Figure 2. On-Resistance vs. Gate-Source Voltage

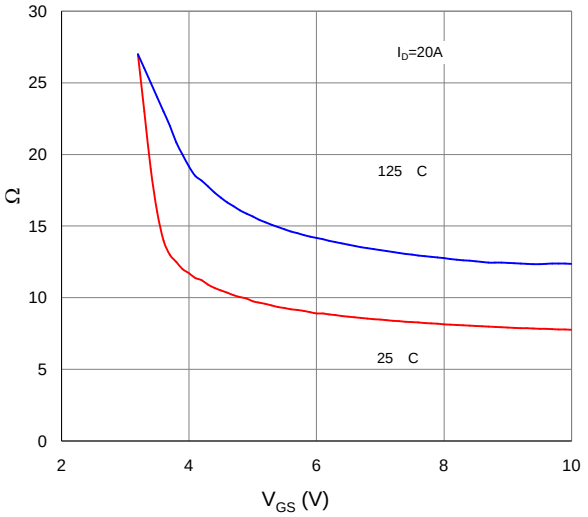


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

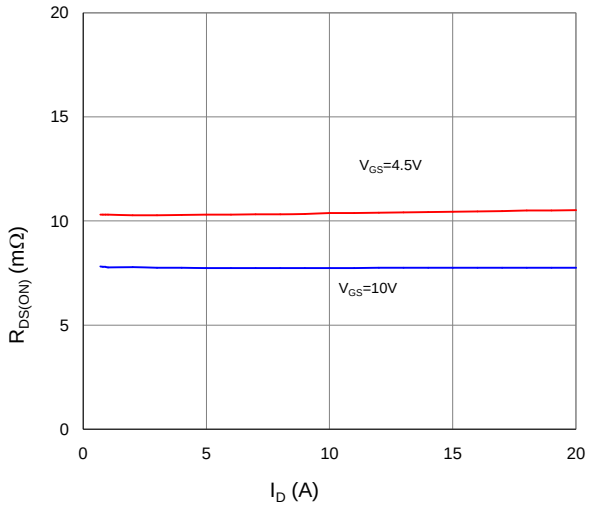


Figure 4. Normalized On-Resistance vs. Junction Temperature

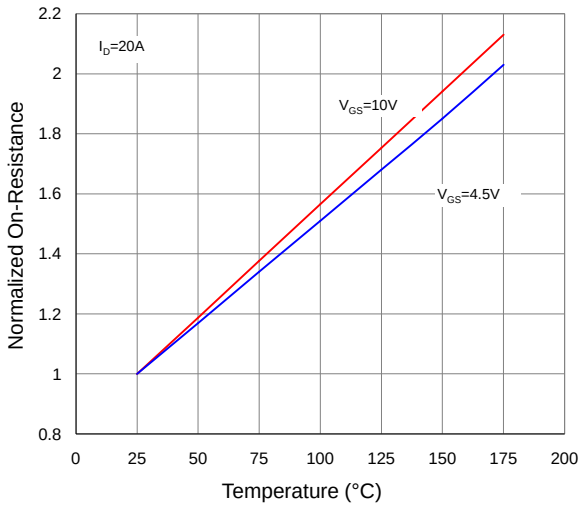


Figure 5. Typical Transfer Characteristics

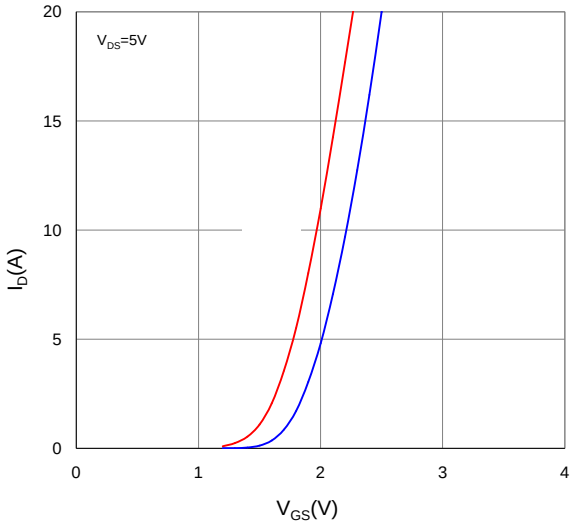


Figure 6. Typical Source-Drain Diode Forward Voltage

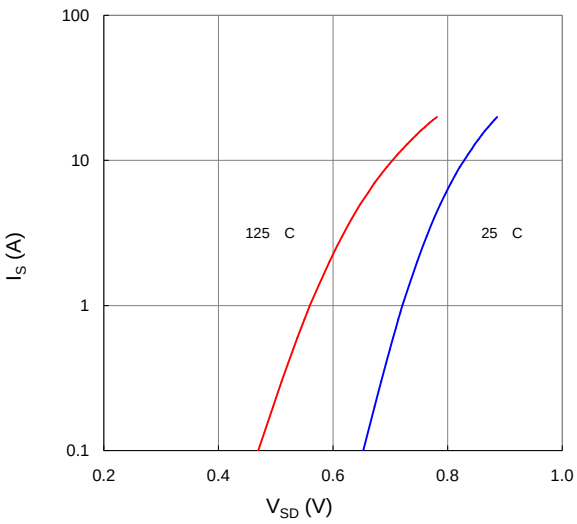


Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

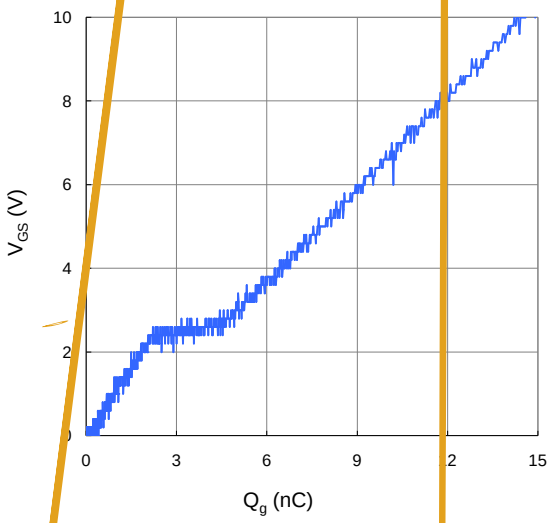


Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

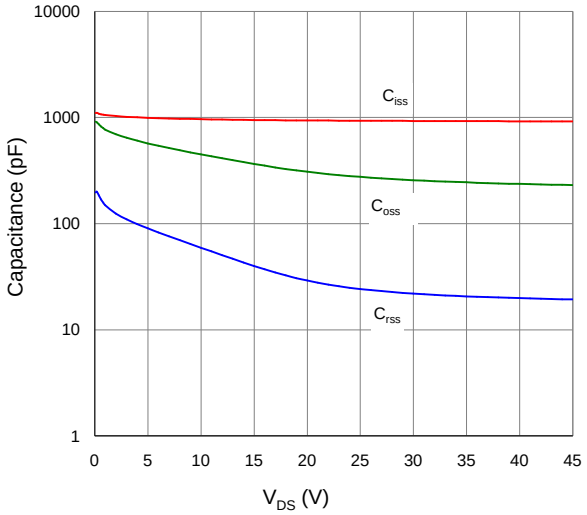


Figure 9. Maximum Safe Operating Area

Figure 10. Maximun Drain Current vs. Case Temperature

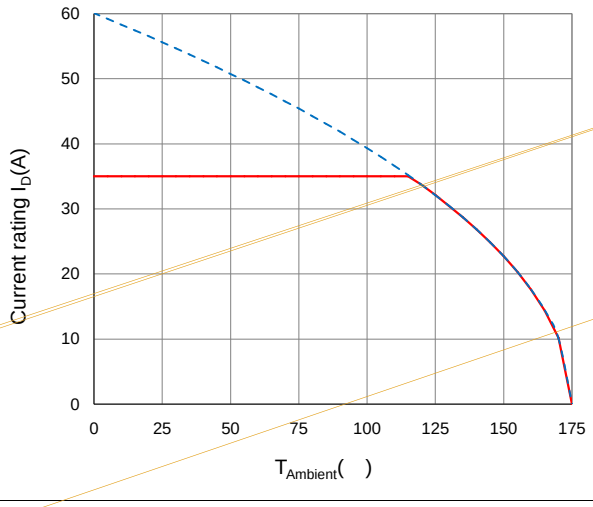
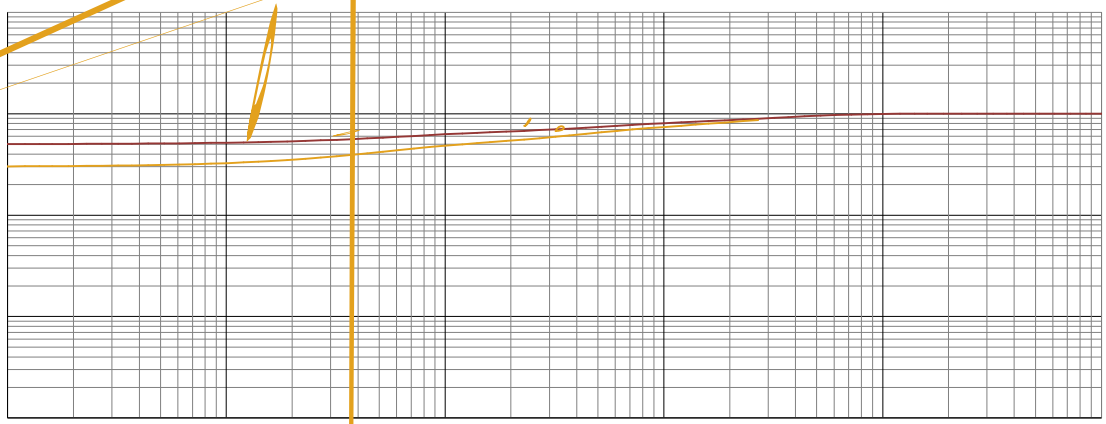


Figure 11. Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient



Inductive switching Test

Gate Charge Test

Uclamped Inductive Switching (UIS) Test